

Delgado Notario, Ja

List of Publications by Year in descending order

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192
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#	ARTICLE	IF	CITATIONS
1	Enhanced terahertz detection of multigate graphene nanostructures. Nanophotonics, 2022, 11, 519-529.	2.9	17
2	Nature of the $1/f$ noise in graphene—direct evidence for the mobility fluctuation mechanism. Nanoscale, 2022, 14, 7242-7249.	2.8	25
3	Responsivity enhancement of a strained silicon field-effect transistor detector at 0.3 THz using the terajet effect. Optics Letters, 2021, 46, 3061.	1.7	10
4	Imaging resolution enhancement using terajet effect at 0.3 THz. , 2021, , .		0
5	Numerical Study of the Coupling of Sub-Terahertz Radiation to n-Channel Strained-Silicon MODFETs. Sensors, 2021, 21, 688.	2.1	1
6	Electromagnetic Simulation of the Sub-THz Radiation Coupling to n-channel strained-silicon MODFETs. , 2021, , .		0
7	Effect of the Front and Back Illumination on Sub-Terahertz Detection Using n-Channel Strained-Silicon MODFETs. Applied Sciences (Switzerland), 2020, 10, 5959.	1.3	3
8	Asymmetric dual-grating gates graphene FET for detection of terahertz radiations. APL Photonics, 2020, 5, 066102.	3.0	36
9	Towards Understanding the Raman Spectrum of Graphene Oxide: The Effect of the Chemical Composition. Coatings, 2020, 10, 524.	1.2	42
10	Improvement of a Terahertz Detector Performance Using the Terajet Effect in a Mesoscale Dielectric Cube: Proof of Concept. Physica Status Solidi - Rapid Research Letters, 2020, 14, 1900700.	1.2	7
11	Comprehensive characterization of Gunn oscillations in $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ planar diodes. Semiconductor Science and Technology, 2020, 35, 115009.	1.0	3
12	Quantum nanoconstrictions fabricated by cryo-etching in encapsulated graphene. Scientific Reports, 2019, 9, 13572.	1.6	16
13	Asymmetric Dual Grating Gate Graphene-based THz detectors. , 2019, , .		0
14	Quantized Electron Transport Through Graphene Nanoconstrictions. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1701065.	0.8	8
15	Continuous Wave Terahertz Sensing Using GaN HEMTs. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700607.	0.8	8
16	Sub-THz Response of Strained-Silicon MODFETs. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700475.	0.8	2
17	Fabrication Process of Non-Linear Planar Diodes Based on GaN. , 2018, , .		0
18	Voltage controlled sub-THz detection with gated planar asymmetric nanochannels. Applied Physics Letters, 2018, 113, .	1.5	13

#	ARTICLE	IF	CITATIONS
19	Sub-THz Imaging Using Non-Resonant HEMT Detectors. Sensors, 2018, 18, 543.	2.1	12
20	Terahertz detection and imaging using an uncooled off-the-shelf GaN High Electron Mobility field-effect Transistor. , 2017, , .		2
21	Asymmetric dual grating gate bilayer graphene FET for detection of terahertz radiation. , 2017, , .		0
22	Experimental and theoretical studies of Sub-THz detection using strained-Si FETs. Journal of Physics: Conference Series, 2017, 906, 012003.	0.3	1
23	Detection of terahertz radiation using submicron field effect transistors and their use for inspection applications. , 2017, , .		0
24	Sub-Micron Gate Length Field Effect Transistors as Broad Band Detectors of Terahertz Radiation. International Journal of High Speed Electronics and Systems, 2016, 25, 1640020.	0.3	9
25	Direct detection of 300GHz using commercial GaAs high electron mobility transistors. , 2016, , .		0
26	Optimization of THz response of strainedâ€Si MODFETs. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 1401-1404.	0.8	2
27	Enhancement of sub-terahertz detection by drain-to-source biasing on strained silicon MODFET devices. Journal of Physics: Conference Series, 2015, 647, 012007.	0.3	2
28	Terahertz spectroscopy of a multilayers flake of graphene. Journal of Physics: Conference Series, 2015, 647, 012040.	0.3	4
29	TCAD study of sub-THz photovoltaic response of strained-Si MODFET. Journal of Physics: Conference Series, 2015, 647, 012041.	0.3	2